# NSN 5961-01-186-5623

Transistor - Page 1 of 2



View Online at https://aerobasegroup.com/nsn/5961-01-186-5623

#### **Inclosure Material:**

Metal

**Overall Length:** 

0.935 inches

# **Mounting Facility Quantity:**

1

#### Internal Configuration:

Junction contact

Joint Electronic Device Engineering Council/jedec/case Outline Designation:

To-60

#### **Mounting Method:**

Threaded stud

#### **Features Provided:**

Hermetically sealed case

#### **Overall Width Across Flats:**

0.437 inches

#### Thread Size:

0.190 inches

#### Semiconductor Material:

Silicon

# Voltage Rating In Volts Per Characteristic:

80.0 breakdown voltage, collector-to-base, emitter open and 4.0 emitter to base voltage, static, collector open and 60.0 breakdown voltage, collector-to-emitter, base open

#### **Current Rating Per Characteristic:**

2.50 amperes source cutoff current

#### **Power Rating Per Characteristic:**

18.0 watts small-signal input power, common-collector

#### **Transfer Ratio:**

115.0 static forward current transfer ratio, common-emitter

# Maximum Operating Tempurature Per Measurement Point:

200.0 degrees celsius junction

# **Special Features:**

Junction pattern arrangement: npn

# **Thread Series Designator:**

Unf

#### Terminal Type And Quantity:

3 uninsulated wire lead and 1 threaded stud

#### Shelf Life:

N/a

#### Unit Of Measure:

---

#### Demilitarization:

No

# **NSN 5961-01-186-5623** Transistor - Page 2 of 2

Fiig: A110a0

